

What is claimed is:

1. A method for gettering a transition metal impurity diffused in a silicon crystal at ultra high-speeds to form deep impurity levels therein, said method comprising the steps of:

codoping two kinds of impurities consisting of oxygen (O) and carbon (C), into silicon; and

thermally annealing said impurity-doped silicon to precipitate an impurity complex comprising an atom of said transition metal impurity, said C and said O, in said silicon crystal, whereby said transition metal impurity is confined in said silicon crystal to prevent the ultra high-speed diffusion of said transition metal impurity and electrically deactivate deep impurity levels to be induced by said transition metal impurity.

2. The method as defined in claim 1, wherein said transition metal impurity is at least one selected from the group consisting of Co, Ni and Cu which are released from a raw material during a process of forming a silicon single crystal and mixed in said silicon crystal, and Cu which is mixed in a silicon wafer during a process of printing a Cu wiring.

3. The method as defined in claim 1, wherein said codoping step includes codoping oxygen (O) in a natural manner and carbon (C) in an artificial manner, or both oxygen (O) and carbon (C) in an artificial manner, into a silicon melt during a silicon single crystal growth through a Czochralski crystal pulling process.

4. The method as defined in claim 1, wherein said codoping step includes ion-injecting an oxygen ion and a carbon ion into a silicon wafer to codope both oxygen (O) and carbon (C) in an artificial manner, into said silicon wafer.